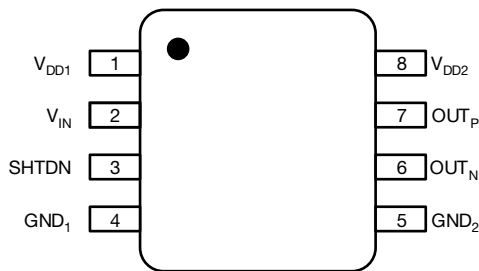
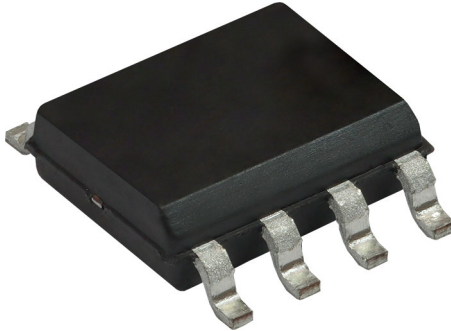


High Reliability Reinforced Isolated Amplifier



LINKS TO ADDITIONAL RESOURCES



AGENCY APPROVALS

- UL
- cUL
- DIN EN 60747-5-5 (VDE 0884-5)
- CQC

DEVICE INFORMATION		
PART NUMBER	PACKAGE	BODY SIZE
VIA2000SD	SOP-8 (300 mil)	5.85 mm x 7.50 mm

ORDERING INFORMATION							
PART NUMBER	ISOLATION RATING (kV)	LINEAR INPUT RANGE (mV)	MOISTURE SENSITIVITY LEVEL	TEMPERATURE (°C)	AUTOMOTIVE	PACKAGE TYPE	SPQ
VIA2000SD	5	100 to 2000	Level 3	-40 to +125	No	SOP-8 (300 mil)	1000

DESCRIPTION

VIA2000SD is a high performance differential output isolation amplifier suited for high precision isolated voltage sensing. The device is based on proprietary capacitive isolation technology and has a single-ended input signal range from 0.02 V to 2 V. The device has a high input impedance making it suitable for measurements across HV potential dividers. The devices unmatched CMTI of 100 kV/ μ s min. allows accurate measurements in the noisy environment.

FEATURES

- Isolation test voltage: 5000 V_{RMS}
- Fixed gain: 1
- Low offset error and drift: ± 1.5 mV (max.), -5 μ V/ $^{\circ}$ C to $+30$ μ V/ $^{\circ}$ C
- Low gain error and drift: ± 0.3 % (max.), ± 45 ppm/ $^{\circ}$ C (max.)
- Low non-linearity and drift: ± 0.05 % (max.), ± 1 ppm/ $^{\circ}$ C (typ.)
- SNR: 70 dB (typ., BW = 100 kHz)
- Wide bandwidth: 400 kHz (typ.)
- High CMTI: 150 kV/ μ s typ.
- Inbuilt V_{DD1} monitoring
- Operating temperature: -40 $^{\circ}$ C to $+125$ $^{\circ}$ C
- Material categorization: for definitions of compliance please see www.vishay.com/doc?99912



RoHS
COMPLIANT
HALOGEN
FREE
GREEN
(5-2008)

APPLICATIONS

- Bus voltage monitoring
- AC motor controls
- Power and solar inverters
- Uninterruptible power suppliers

Note

- For automotive qualification please contact our local sales.

ABSOLUTE MAXIMUM RATINGS ($T_{amb} = 25\text{ }^{\circ}\text{C}$, unless otherwise specified)			
PARAMETER	SYMBOL	VALUE	UNIT
Power supply voltage	V_{DD1}, V_{DD2}	-0.3 to 6.5	V
Input voltage	V_{IN}	GND_{1-6} to $V_{DD1+0.5}$	V
	SHTDN	$\text{GND}_{1-0.5}$ to $V_{DD1+0.5}$	V
Output voltage	$\text{OUT}_P, \text{OUT}_N$	$\text{GND}_{2-0.5}$ to $V_{DD2+0.5}$	V
Output current per output pin	I_O	-10 to +10	mA
Operating temperature	T_{amb}	-40 to +125	$^{\circ}\text{C}$
Junction temperature	T_j	-40 to +150	$^{\circ}\text{C}$
Storage temperature	T_{stg}	-55 to +150	$^{\circ}\text{C}$
Electrostatic discharge	HBM ⁽¹⁾	± 2000	V
	CDM ⁽²⁾	± 1000	V

Notes

- (1) Human body model (HBM), per AEC-Q100-002-RevD
 (2) Charged device model (CDM), per AEC-Q100-011-RevB

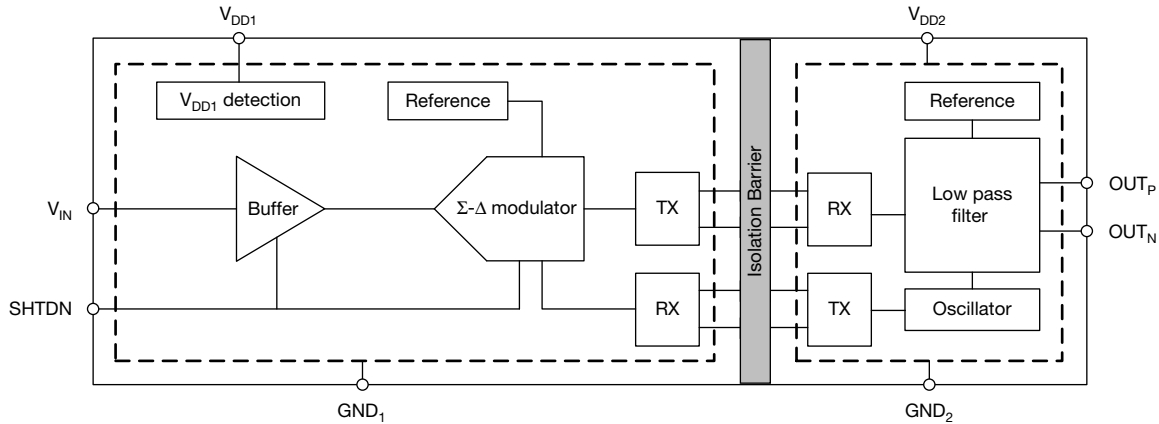
FUNCTIONAL BLOCK DIAGRAM


Fig. 1 - VIA2000SD Block Diagram

RECOMMENDED OPERATING CONDITIONS ($T_{amb} = 25\text{ }^{\circ}\text{C}$, unless otherwise specified)						
PARAMETER	SYMBOL	MIN.	TYP.	MAX.	UNIT	
Side 1 power supply	V_{DD1}	3.0	5.0	5.5	V	
Side 2 power supply	V_{DD2}	3.0	3.3	5.5	V	
VIA2000SD	Differential input voltage before clipping output	$V_{clipping}$	-	2.56	-	V
	Linear differential input full scale voltage	V_{FSR}	0.02	-	2	V
	Digital input voltage	SHTDN	GND_1	-	V_{DD1}	
Operating ambient temperature	T_{amb}	-40	-	+125	$^{\circ}\text{C}$	

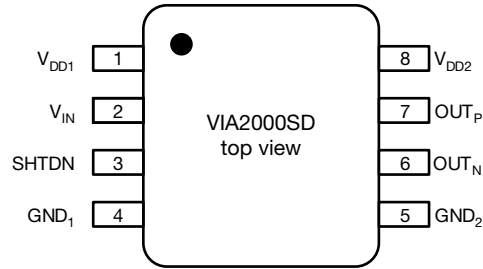
PIN CONFIGURATION AND FUNCTIONS


Fig. 2 - VIA2000SD Package

PIN CONFIGURATION AND DESCRIPTION		
PIN NO.	SYMBOL	FUNCTION
1	V_{DD1}	Power supply for isolator side 1 (3.0 V to 5.5 V)
2	V_{IN}	Analog input
3	SHTDN	Shutdown input, active high, pulled up internally (typical resistor value: 100 k Ω)
4	GND_1	Ground 1, the ground reference for isolator side 1
5	GND_2	Ground 2, the ground reference for isolator side 2
6	OUT_N	Negative output
7	OUT_P	Positive output
8	V_{DD2}	Power supply for isolator side 2 (3.0 V to 5.5 V)



ELECTRICAL CHARACTERISTICS: VIA2000SD ($V_{DD1}, V_{DD2} = 3\text{ V to }5.5\text{ V}, V_{IN} = 0.1\text{ V to }2\text{ V}, \text{ and SHTDN} = \text{GND}_1 = 0\text{ V}, T_{\text{amb}} = -40\text{ }^{\circ}\text{C to }+125\text{ }^{\circ}\text{C}$) ($V_{DD1} = 5\text{ V}, V_{DD2} = 3.3\text{ V}, T_{\text{amb}} = 25\text{ }^{\circ}\text{C}, \text{ unless otherwise noted}$)						
PARAMETER	TEST CONDITION	SYMBOL	MIN.	TYP.	MAX.	UNIT
POWER SUPPLY						
Side 1 supply voltage		V_{DD1}	3.0	5.0	5.5	V
Side 2 supply voltage		V_{DD2}	3.0	3.3	5.5	V
Side 1 supply current	SHTDN = low	I_{DD1}	-	11.4	15.1	mA
	SHTDN = high		-	1	-	μA
Side 2 supply current		I_{DD2}	-	6.3	8.4	mA
V_{DD1} undervoltage detection threshold voltage	V_{DD1} falling	V_{DD1_UV}	1.8	2.3	2.7	V
ANALOG INPUT						
Input offset voltage	$V_{IN} = 1\text{ V}$	V_{OS}	-1.5	± 0.4	+1.5	mV
Input offset drift		TCV_{OS}	-5	10	30	$\mu\text{V}/^{\circ}\text{C}$
Input resistance		R_{IN}	-	1	-	$\text{G}\Omega$
Input capacitance	$f_{IN} = 275\text{ kHz}$	C_{IN}	-	7	-	pF
Input bias current	$V_{IN} = \text{GND}_1$	I_{IB}	-15	3.5	15	nA
Input bias current drift		TCI_{IB}	-	± 10	-	$\text{pA}/^{\circ}\text{C}$
ANALOG OUTPUT						
Nominal gain			-	1	-	V/V
Gain error		E_G	-0.3	± 0.05	+0.3	%
Gain error thermal drift		TCE_G	-45	± 5	+45	$\text{ppm}/^{\circ}\text{C}$
Non-linearity			-0.04	± 0.01	+0.04	%
Non-linearity drift			-	± 1	-	$\text{ppm}/^{\circ}\text{C}$
Total harmonic distortion	$V_{IN} = 1.8\text{ V}, f_{IN} = 10\text{ kHz}, \text{ BW} = 100\text{ kHz}$	THD		-87	-	dB
Output noise	$V_{IN} = 1\text{ V}, \text{ BW} = 100\text{ kHz}$		-	210	-	μV_{RMS}
Signal to noise ratio	$V_{IN} = 1.8\text{ V}, f_{IN} = 1\text{ kHz}, \text{ BW} = 10\text{ kHz}$	SNR	78	82	-	dB
	$V_{IN} = 1.8\text{ V}, f_{IN} = 10\text{ kHz}, \text{ BW} = 100\text{ kHz}$		-	70	-	dB
Common-mode output voltage		V_{CMout}	1.36	1.4	1.45	V
Fail-safe differential output voltage	SHTDN active or V_{DD1} missing	$V_{\text{Fail-Safe}}$	-	-2.53	-2.44	V
Output bandwidth		BW	-	400	-	kHz
Power supply rejection ratio ⁽¹⁾	PSRR vs. V_{DD1} , at DC	PSRR_{DC}	-	-78	-	dB
	PSRR vs. V_{DD1} , 100 mV and 10 kHz ripple	PSRR_{AC}	-	-75	-	dB
	PSRR vs. V_{DD2} , at DC	PSRR_{DC}	-	-82	-	dB
	PSRR vs. V_{DD2} , 100 mV and 10 kHz ripple	PSRR_{AC}	-	-74	-	dB
Output resistance		R_{OUT}	-	< 0.2	-	Ω
Common-mode transient immunity		CMTI	100	150	-	$\text{kV}/\mu\text{s}$
DIGITAL INPUT (SHTDN)						
Input current	$\text{GND}_1 \leq V_{\text{SHTDN}} \leq V_{DD1}$	I_{IN}	-70		1	μA
Input capacitance		C_{IN}	-	5	-	pF
High level input voltage		V_{IH}	$0.7 \times V_{DD1}$	-	$V_{DD1} + 0.3$	$\text{ppm}/^{\circ}\text{C}$
Low level input voltage		V_{IL}	-0.3	-	$0.3 \times V_{DD1}$	%
TIMING						
Rising time of $\text{OUT}_P, \text{OUT}_N$		t_r	-	1.3	-	μs
Falling time of $\text{OUT}_P, \text{OUT}_N$		t_f	-	1.3	-	μs
IN_P, IN_N to $\text{OUT}_P, \text{OUT}_N$ signal delay (50 % to 50 %)		t_{PD}	-	1.6	2.1	μs
Analog setting time	V_{DD1} step to 3.0 V with $V_{DD2} \geq 3.0\text{ V}$, to $\text{OUT}_P, \text{OUT}_N$ valid, 0.1 % settling	t_{AS}	-	0.5	-	ms
Device enable time	SHTDN high to low	t_{EN}	-	80	100	μs
Shutdown time	SHTDN low to high	t_{SHTDN}	-	1.2	5	μs

Note

⁽¹⁾ Input referred



THERMAL INFORMATION			
PARAMETER	SYMBOL	VALUE	UNIT
Junction to ambient thermal resistance	$R_{\theta JA}$	86	$^{\circ}C/W$
Junction to case (top) thermal resistance	$R_{\theta JC(top)}$	28	$^{\circ}C/W$
Junction to board thermal resistance	$R_{\theta JB}$	42	$^{\circ}C/W$
Junction to top characterization parameter	Ψ_{JT}	4	$^{\circ}C/W$
Junction to board characterization parameter	Ψ_{JB}	42	$^{\circ}C/W$

TYPICAL CHARACTERISTICS

(Unless otherwise noted, $V_{DD1} = 5 V$, $V_{DD2} = 3.3 V$, $0.1 V$ to $2 V$, and $SHTDN = GND_1 = 0 V$, $f_{IN} = 1 kHz$, $BW = 10 kHz$)

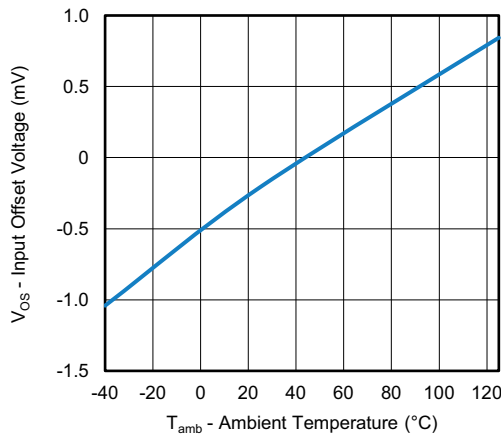


Fig. 3 - Input Offset Voltage vs. Ambient Temperature

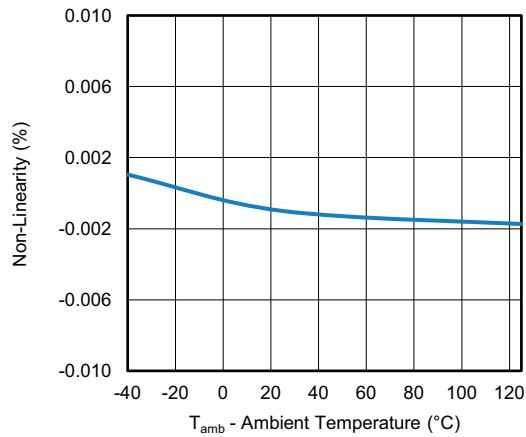


Fig. 5 - Non-Linearity vs. Ambient Temperature

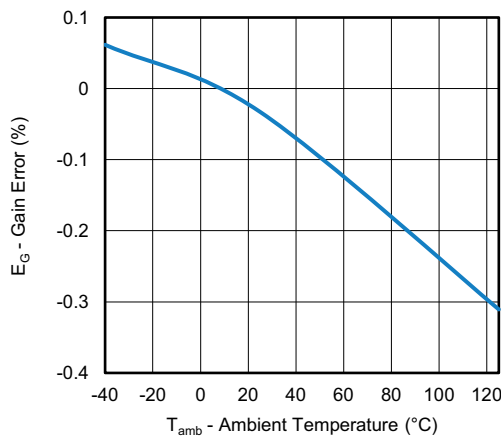


Fig. 4 - Gain Error vs. Ambient Temperature

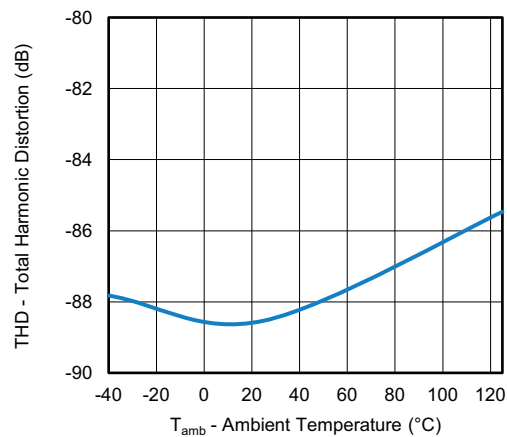


Fig. 6 - Total Harmonic Distortion vs. Ambient Temperature

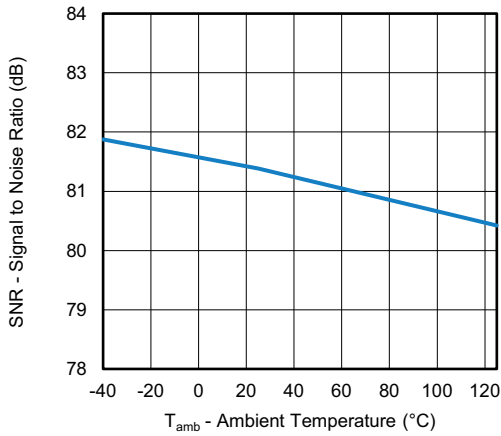


Fig. 7 - Signal to Noise Ratio vs. Ambient Temperature

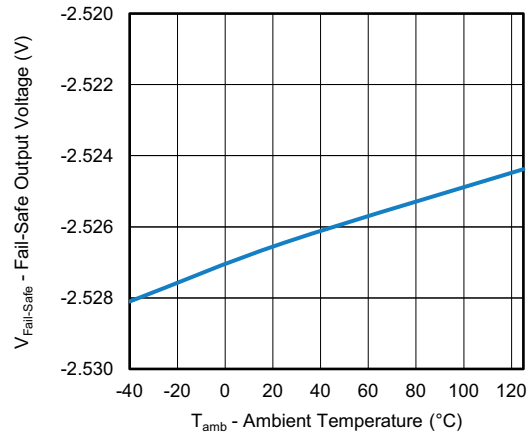


Fig. 10 - Fail-Safe Output Voltage vs. Ambient Temperature

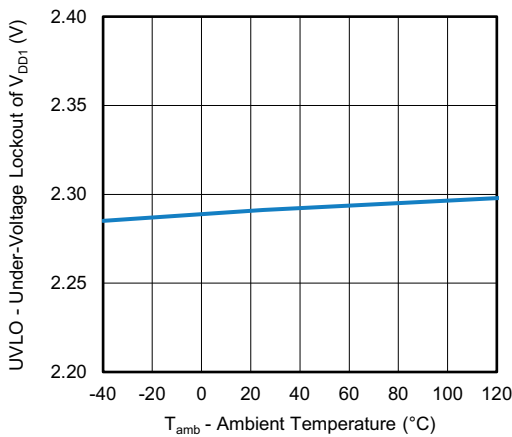


Fig. 8 - Under-Voltage Lockout of V_{DD1} vs. Ambient Temperature

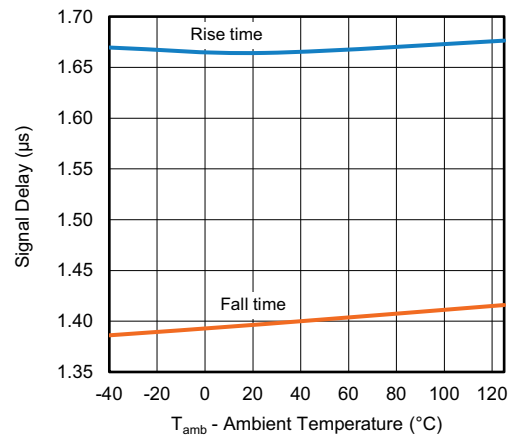


Fig. 11 - Signal Delay vs. Ambient Temperature

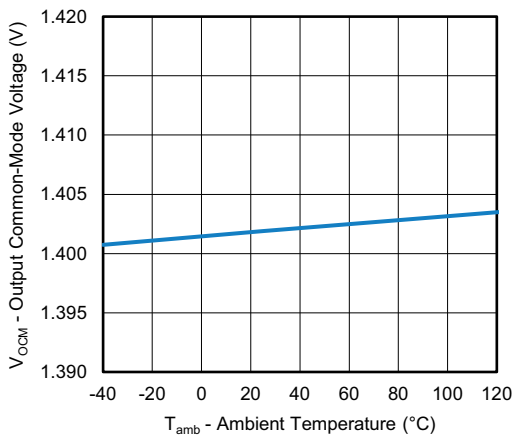


Fig. 9 - Output Common-Mode Voltage vs. Ambient Temperature

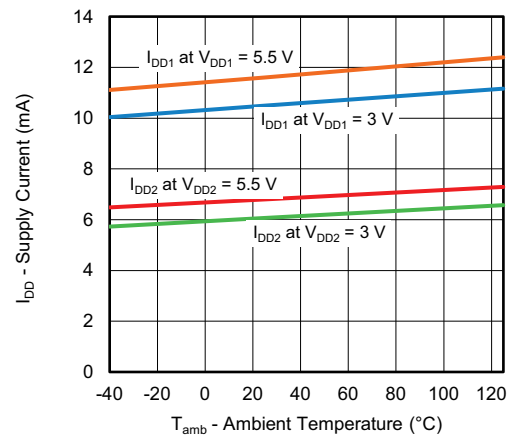


Fig. 12 - Supply Current vs. Ambient Temperature

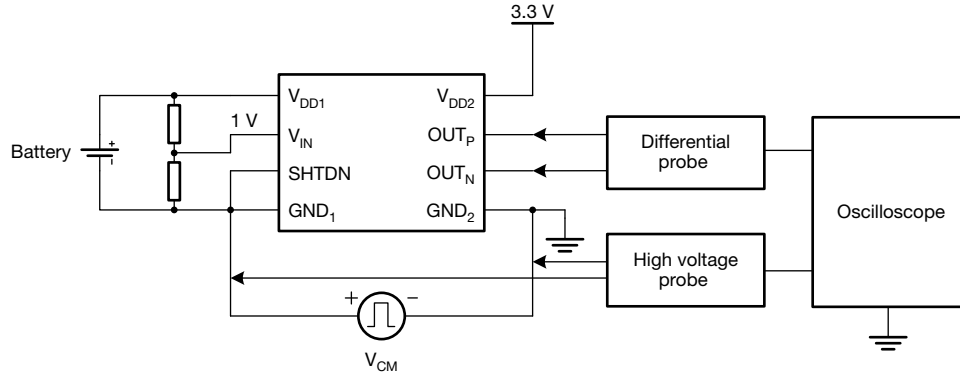
PARAMETER MEASUREMENT INFORMATION


Fig. 13 - Common-Mode Transient Immunity Test Circuit

SAFETY AND INSULATION RATINGS				
PARAMETER	TEST CONDITION	SYMBOL	VALUE	UNIT
Climatic classification	According to IEC 68 part 1		40 / 125 / 21	
Comparative tracking index	DIN EN 60112 (VDE 0303-11); IEC 60112	CTI	> 600	
Maximum rated withstanding isolation voltage	$V_{TEST} = V_{ISO}$, $t = 1$ min (qualification); $V_{TEST} = 1.2 \times V_{ISO}$, $t = 1$ s (100 % production test)	V_{ISO}	5000	V_{RMS}
Maximum transient isolation voltage	$t = 1$ min	V_{IOTM}	8000	V_{peak}
Maximum repetitive isolation voltage		V_{IORM}	2121	V_{peak}
Maximum surge isolation voltage	Test method per IEC 60065, 1.2/50 μ s waveform, $V_{TEST} = V_{IOSM} \times 1.6$	V_{IOSM}	6250	V_{peak}
Maximum working isolation voltage	AC voltage	V_{IOWM}	1500	V_{RMS}
	DC voltage		2121	V_{DC}
Isolation resistance	$T_{amb} = 25$ °C, $V_{IO} = 500$ V	R_{IO}	$> 10^{12}$	Ω
	$T_{amb} = 125$ °C, $V_{IO} = 500$ V	R_{IO}	$> 10^{10}$	Ω
	$T_{amb} = 150$ °C, $V_{IO} = 500$ V	R_{IO}	$> 10^9$	Ω
Total power dissipation at 25 °C	$\theta_{JA} = 86$ °C/W, $V_I = 5.5$ V, $T_j = 150$ °C, $T_{amb} = 25$ °C	P_S	1430	mW
Safety input, output, or supply current	$\theta_{JA} = 86$ °C/W, $V_I = 5.5$ V, $T_j = 150$ °C, $T_{amb} = 25$ °C	I_S	260	mA
Maximum safety temperature		T_S	150	°C
Creepage distance	SOP-8 (300 mils)		≥ 8	mm
Clearance distance			≥ 8	mm
Insulation thickness	Distance through insulation	DTI	28	μ m
Material group	IEC 60664-1		I	
For rated mains voltage $\leq 150 V_{RMS}$			I to IV	
For rated mains voltage $\leq 300 V_{RMS}$			I to IV	
For rated mains voltage $\leq 400 V_{RMS}$			I to IV	
Pollution degree per DIN VDE 0110, table 1			2	
Input to output test voltage, method B1	$V_{IORM} \times 1.875 = V_{pd(m)}$, 100 % production test; $t_{ini} = t_m = 1$ s, partial discharge < 5 pC	$V_{pd(m)}$	3977	V_{peak}
After environmental tests subgroup 1	$V_{IORM} \times 1.6 = V_{pd(m)}$, $t_{ini} = 1$ s, $t_m = 10$ s, partial discharge < 5 pC	$V_{pd(m)}$	3394	V_{peak}
After input and / or safety test subgroup 2 and subgroup 3	$V_{IORM} \times 1.2 = V_{pd(m)}$, $t_{ini} = 1$ s, $t_m = 10$ s, partial discharge < 5 pC	$V_{pd(m)}$	2545	V_{peak}
Isolation capacitance	$f = 1$ MHz	C_{IO}	0.8	pF

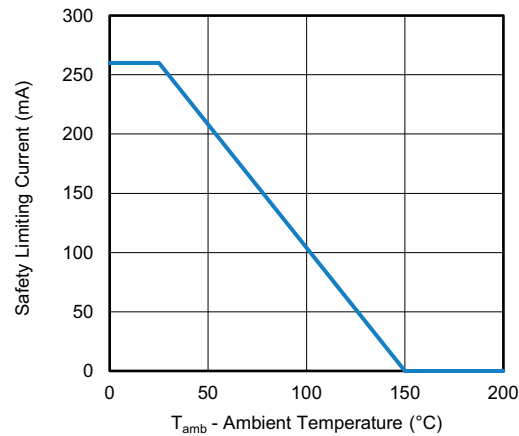


Fig. 14 - VIA2000SD Thermal Derating Curve, Dependence of Safety Limiting Values With Case Temperature per DIN VOE V0884-11

FUNCTION DESCRIPTION

Overview

The VIA2000SD is a high performance isolated amplifier with a high input impedance that accept wide range single-ended input. The singled-ended input is suited to bus voltage monitoring in high voltage applications where isolation is required. The analog input is continuously sampled by a second-order $\Sigma - \Delta$ modulator in the device. With the internal voltage reference and clock generator, the modulator convert the analog input signal to a digital bitstream. The output of the modulator is transferred by the drivers (called TX in the functional block diagram) across the isolation barrier that separates the isolated side 1 and side 2 voltage. The received bitstream and clock are synchronized and processed, as shown in the functional block diagram, by a fourth-order analog filter on the side 2 and has a differential output.

SHTDN pin is used to disable the conversion. Since SHTDN is an active high signal and is pulled up by a 100 k Ω (typical) internally, it should be connected to GND₁ or logic low in normal operation.

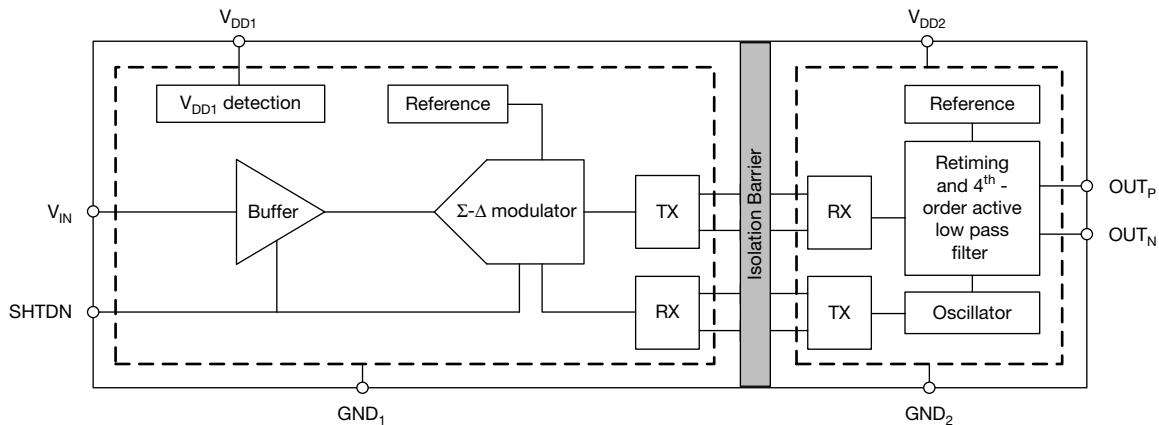


Fig. 15 - Function Block Diagram

Analog Input

Below mentioned are the restrictions on the analog input signal (V_{IN}).

1. If the input voltage exceeds the range $GND_1 - 6\text{ V}$ to $V_{DD1} + 0.5\text{ V}$, the input current must be limited to 10 mA because the device input electrostatic discharge (ESD) diodes turn on
2. The linearity and noise performance of the device are ensured only when the analog input voltage remains within the specified linear full-scale range (FSR)

Analog Output

For linear input range, VIA2000SD provides an analog differential output which has a fixed gain of 1. If a full-scale input signal is applied to the VIA2000SD ($V_{IN} \geq V_{Clipping}$), the analog output will be clipped.

In addition, VIA2000SD integrates some diagnostic measures and offers a fail-safe output to simplify system-level design. The fail safe output is a negative differential output voltage that is activated in the conditions mentioned below. Please note that the fail safe output does not occur during normal operation.

1. When the undervoltage of V_{DD1} is detected ($V_{DD1} < V_{DD1uv}$)
2. When SHTDN signal is activated (pulled high)

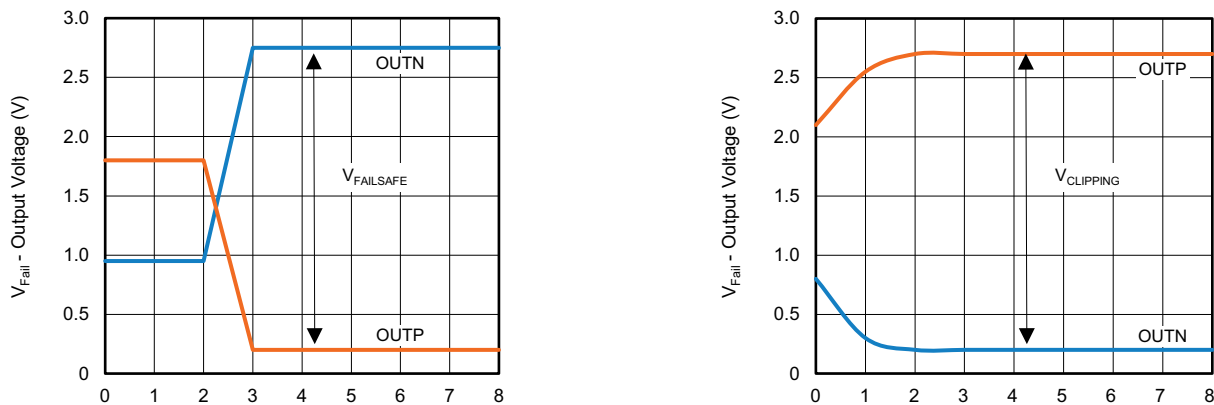


Fig. 16 - Typical Fail-Safe Output When Clipping Output

APPLICATION NOTE
Typical Application Circuit

VIA2000SD has an input impedance of up to 1 GΩ, and has a wide input voltage range as well. These features make VIA2000SD ideally suitable for isolated voltage sensing applications such as frequency inverters. The typical application circuit is shown in Fig. 17.

The bus voltage of the frequency inverter is divided by a resistance network, and the divided voltage is applied to the input of VIA2000SD through a RC filter. The differential output of the isolated amplifier is converted to a single-ended analog output with an operational amplifier based circuit. An analog to digital converter usually receives the analog output and converts to digital signal for controller processing.

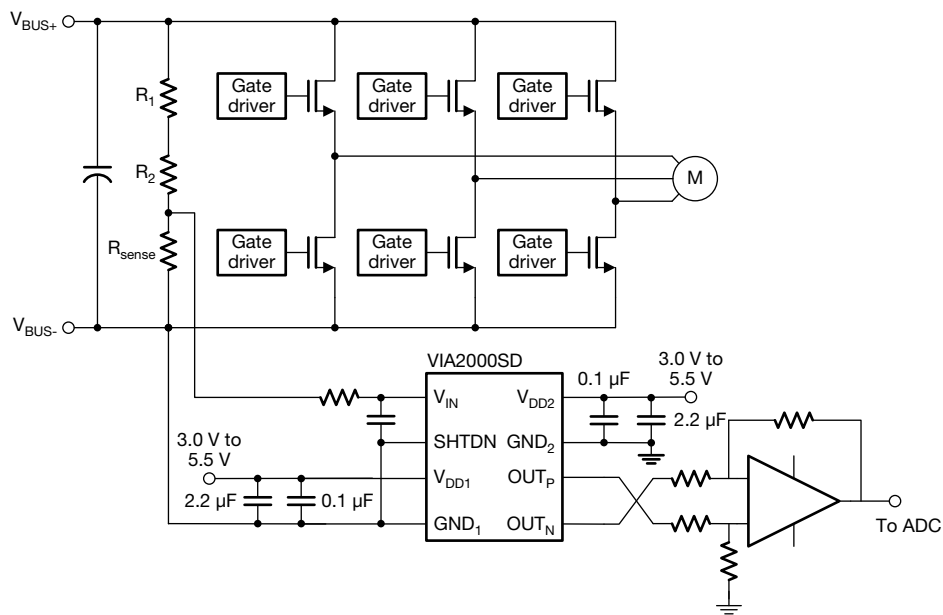


Fig. 17 - Typical Application Circuit in Voltage Sensing

Shunt Resistor Selection

There are two other factors should be considered when selecting the sense resistor:

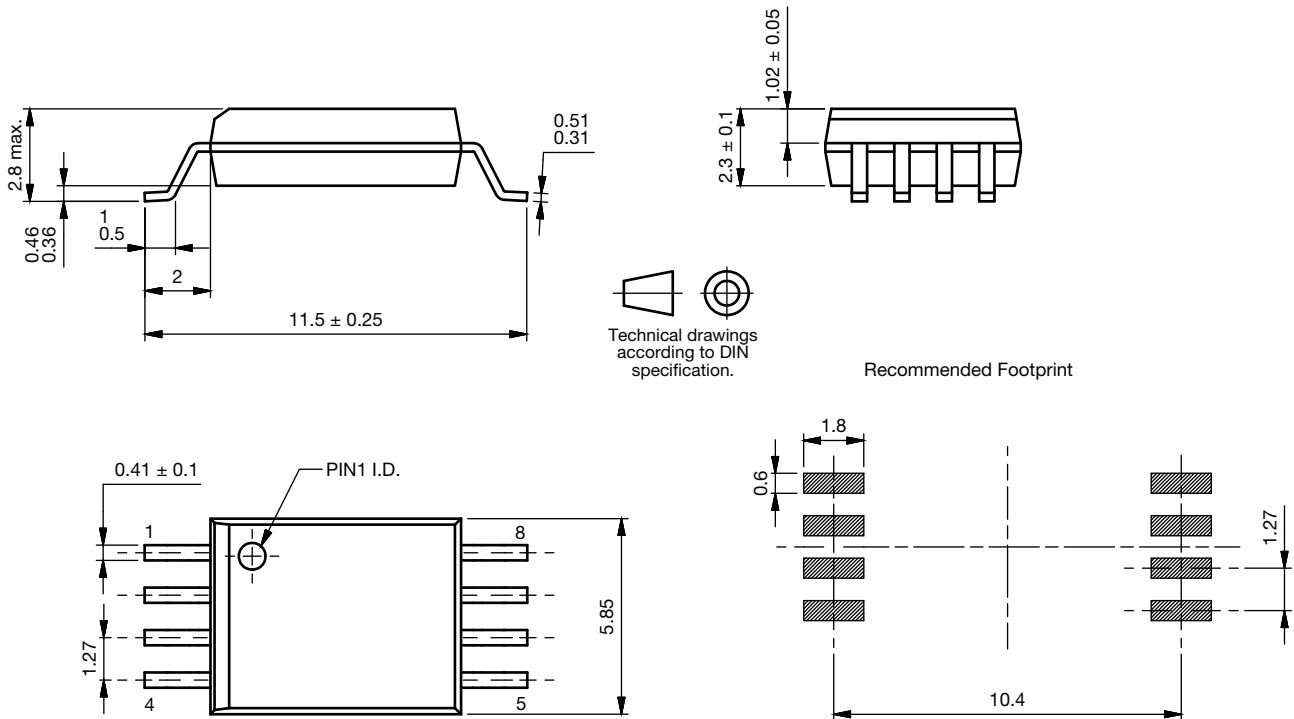
- The voltage-drop on R_{sense} divided by nominal V_{BUS} must not exceed the recommended linear input voltage range: $V_{IN} \leq FSR$
- The voltage-drop on R_{sense} divided by V_{BUS} in maximum allowed overvoltage condition must not exceed the input voltage that causes a clipping output: $V_{IN} \leq V_{Clipping}$

PCB Layout

There are some key guidelines or considerations for optimizing performance in PCB layout:

- VIA2000SD requires a 0.1 μF bypass capacitor between V_{DD1} and GND_1 , V_{DD2} and GND_2 . The capacitor should be placed as close as possible to the V_{DD} pin. If better filtering is required, an additional 1 μF to 10 μF capacitor may be used

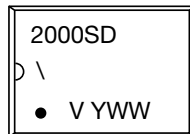
PACKAGE DIMENSIONS (in millimeters)



Drawing-No.: 6.544-5451.1-4
Issue: 1VK; 12.02.2024

Fig. 18 - SOP-8 (300 mil) Package Shape and Dimensions

PACKAGE MARKING (example)



Note

- Tape and reel suffix (TR) is not part of the package marking.



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